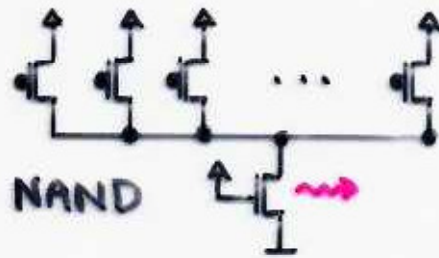
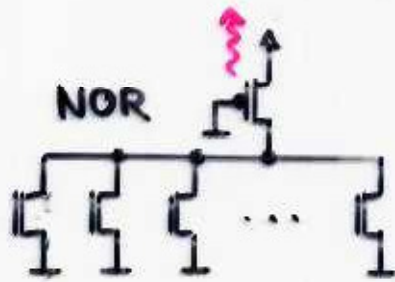
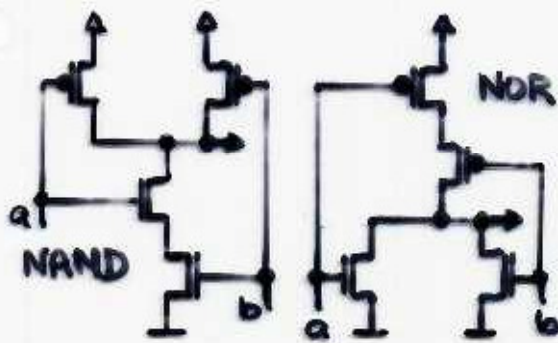


Statische Logik : Typen

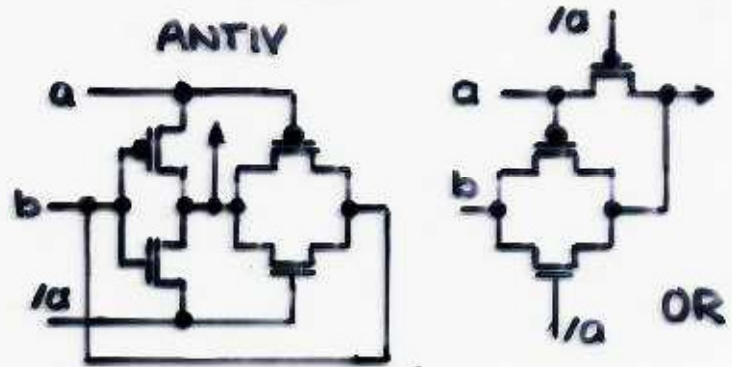
① **Verhältnislogik** Stromverh. I_p/I_n ; $R_{stat} \uparrow$; $A \downarrow$; $\tau \downarrow$; $C_e \downarrow$



② **Komplementärlogik**
 $C_e \uparrow$; $A \uparrow$; $\tau \uparrow$



③ **Schalterlogik**
 $A \downarrow$; $C_e \downarrow$; $\tau \uparrow$

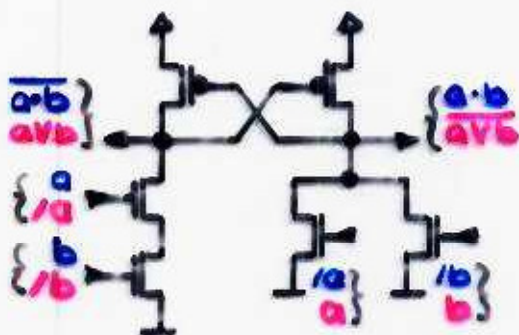
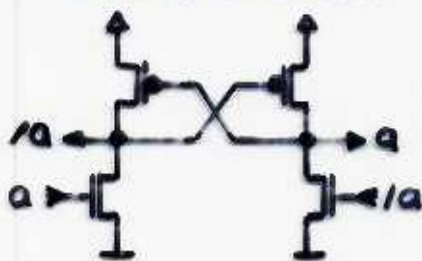


④ **Spiegellogik**

$C_e \downarrow$; $P_{dyn} \uparrow$; $A \uparrow$; $\tau \downarrow$

(Cascode voltage switch logic: CVSL)

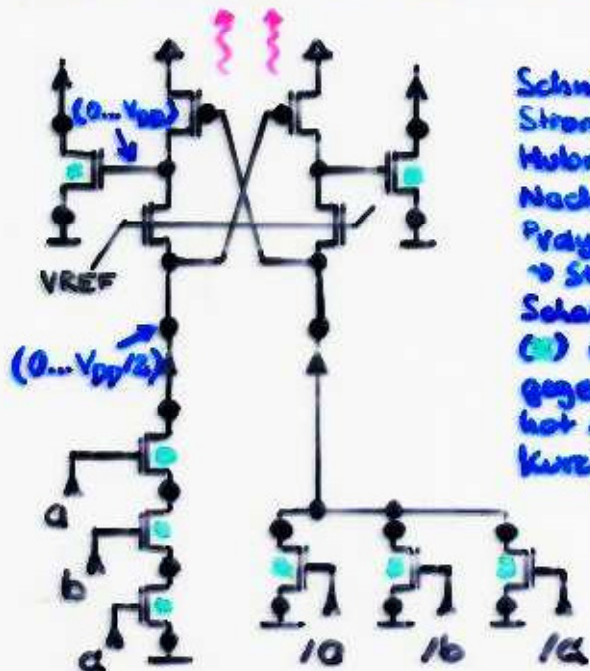
Triber / Inverter:



⑤ **Differenzlogik**

$C_e \downarrow$; $H_{ab} \downarrow$; $P_{dyn} \uparrow$; $\tau \downarrow$; $R_{stat} \uparrow$; $A \uparrow$

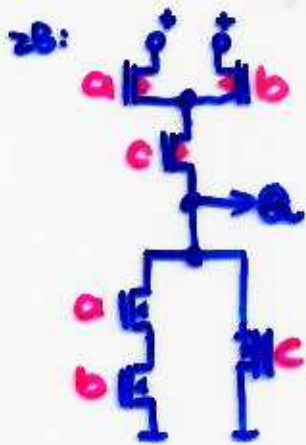
(Differential split-level logic: DSL)



Schnellste Logik:
Stromtrigger &
Hubreduzierung.
Nachteile:
 $P_{dyn} \uparrow$; $H_{ab} \downarrow$
 \rightarrow Störsicher, bei
Schalttransistoren
(\odot) unempfindl.
gegen V_{DD} -Induz.
hat ebenfalls:
Kurzkanal mögl.

KOMPLEMENTÄRLOGIK: (CMOS)

Standardform \rightarrow Ziel: statisch Verlustleistungsfrei:

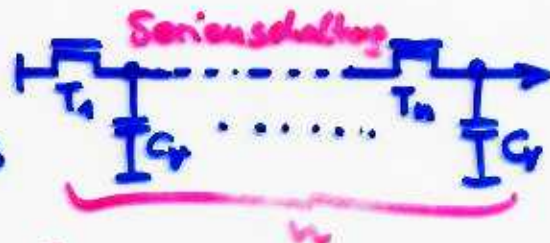
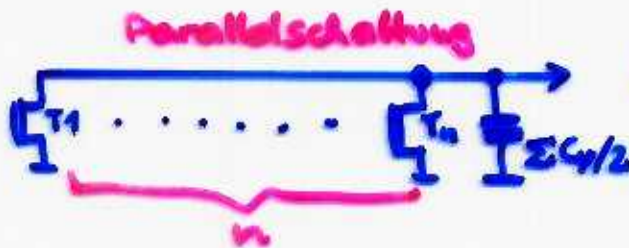


p-Teil $\rightarrow (ab) V_c = \overline{(\bar{a} \vee \bar{b})} \bar{c}$

n-Teil $\rightarrow \overline{(ab) V_c} = (\bar{a} \vee \bar{b}) \bar{c}$

Problem:
großer
Flächen-
bedarf für
Kapazitäten
(Kondensatoren!)

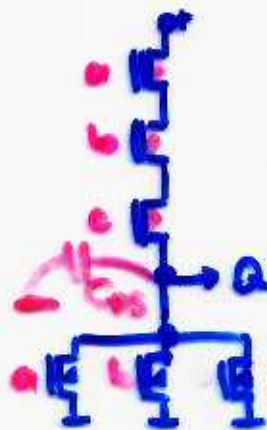
Serien- oder Parallelschaltung?



\hookrightarrow Laufzeitkette: ungünstig.

VERHÄLTNISLOGIK: (CMOS, NMOS)

! statischer Ruhestrom!

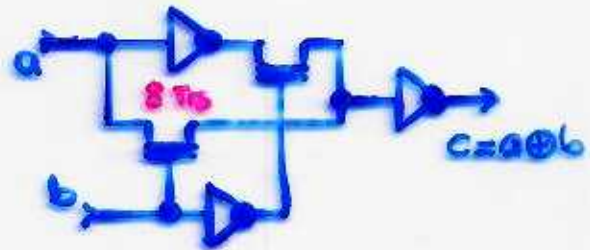
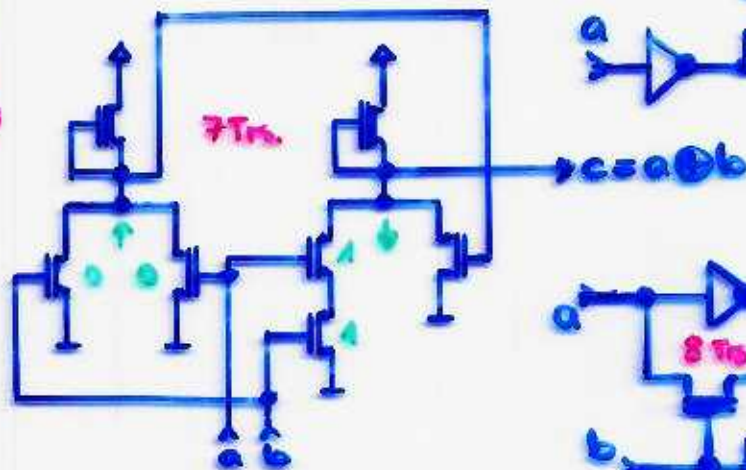


$C_{p0} \approx \frac{1}{2} C_{n0} \rightarrow$ Geschwindigkeitsvorteile nur bei großen, externen Lasten

ANTIVALENZ / AEQUIVALENZ

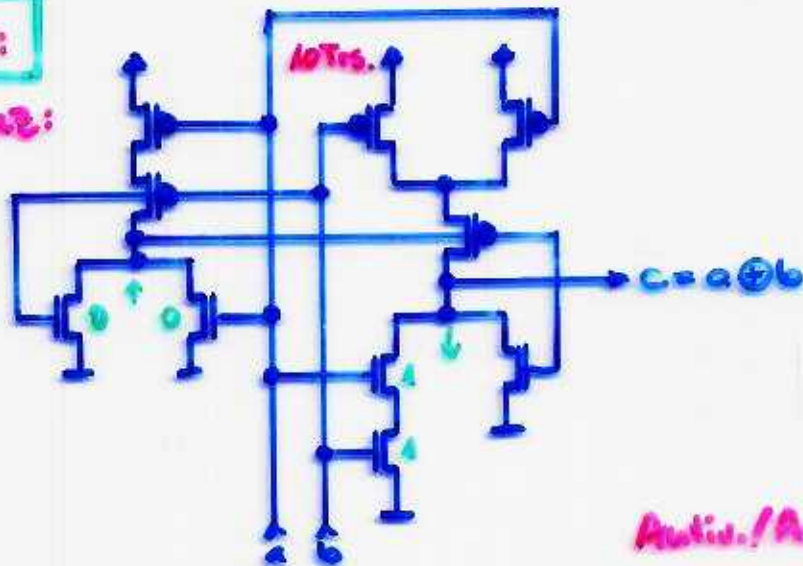
NMOS:

Antivalenz:



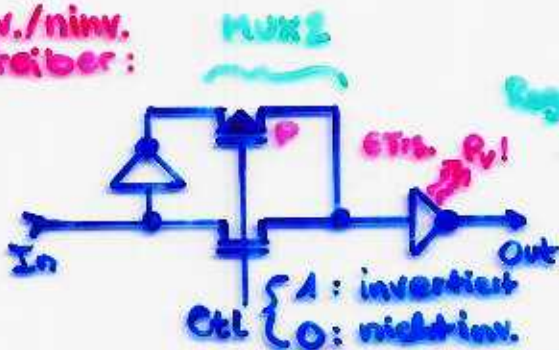
CMOS:

Antivalenz:

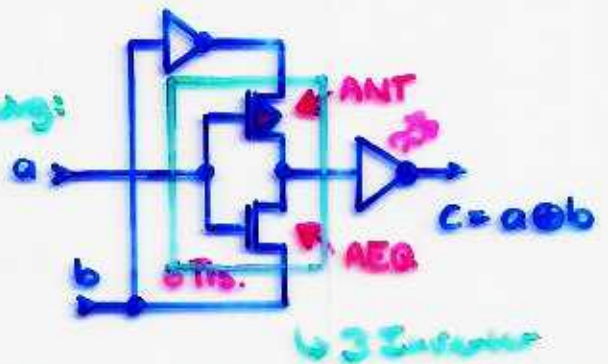


Antiv./Aequivalenz:

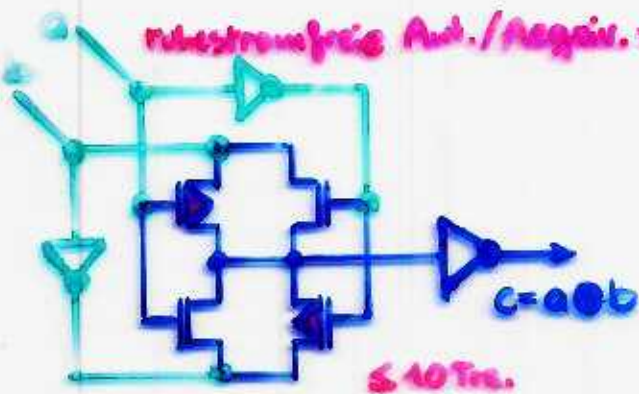
inv./niv. Treiber:



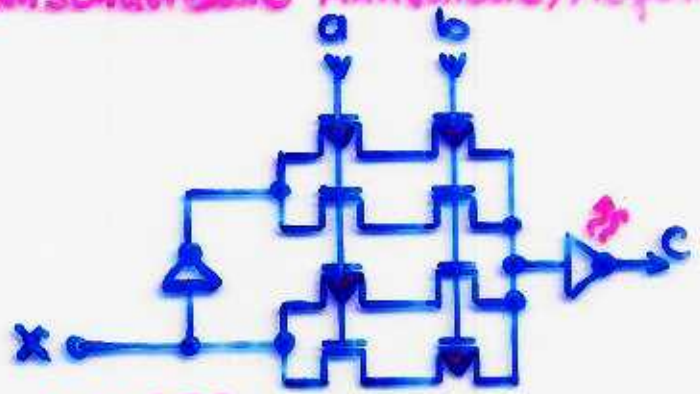
Systemizing:



stromfreie Ant./Aequiv.:



Um-schaltbare Antivalenz/Aequivalenz:

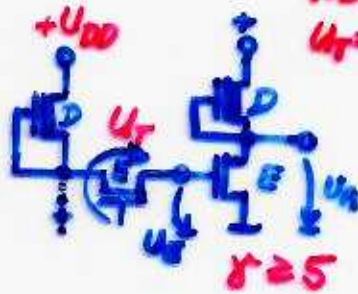


ED-Inv.



$\beta \geq 3,5$

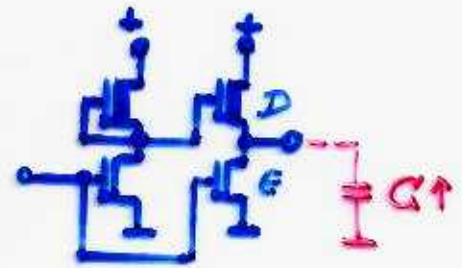
ED-Inv.



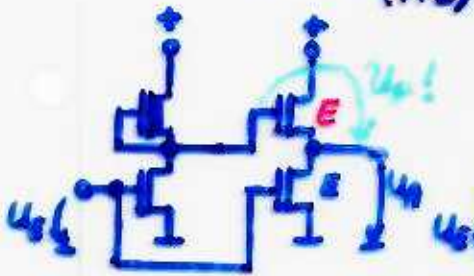
$\beta \geq 5$

nSGT:
 $U_T = 0,2 U_{DD}$

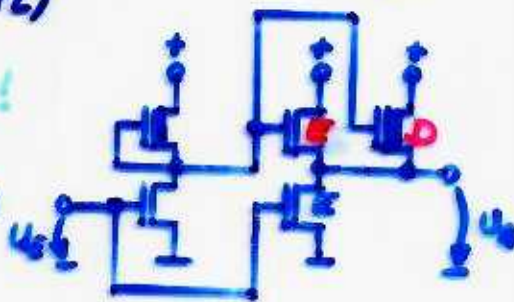
inv. Superbuffer



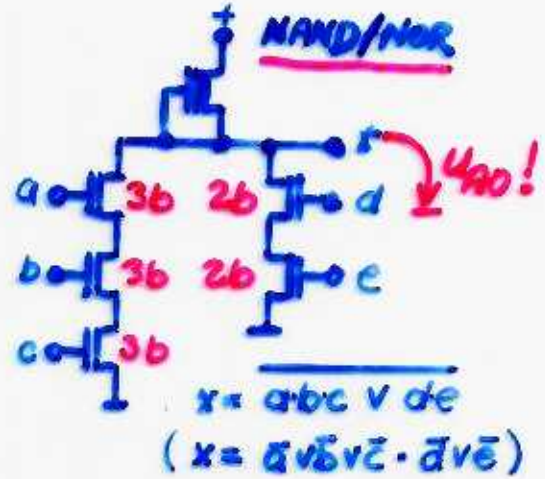
EE-Superbuffer (TTL)



EED-Superbuffer

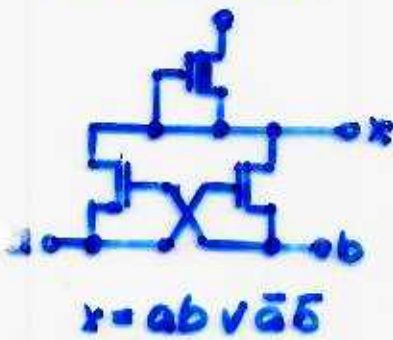


NAND/NOR



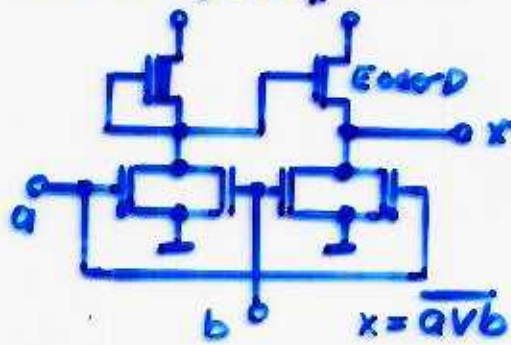
$(x = \bar{a}\bar{b}\bar{c} \cdot \bar{d}\bar{e})$

Äquivalenz



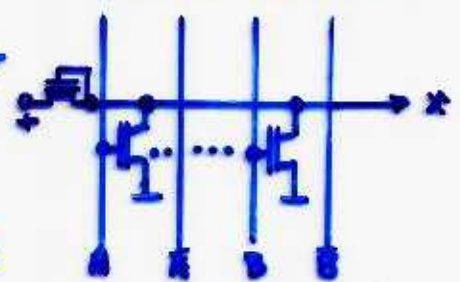
$x = ab \vee \bar{a}\bar{b}$

NOR-Superbuffer

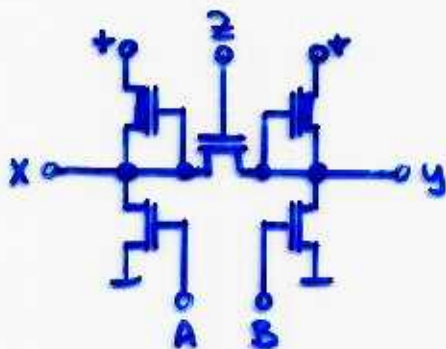


$x = \overline{a\bar{b}}$

DECODER (NOR)



Schalt-NOR:

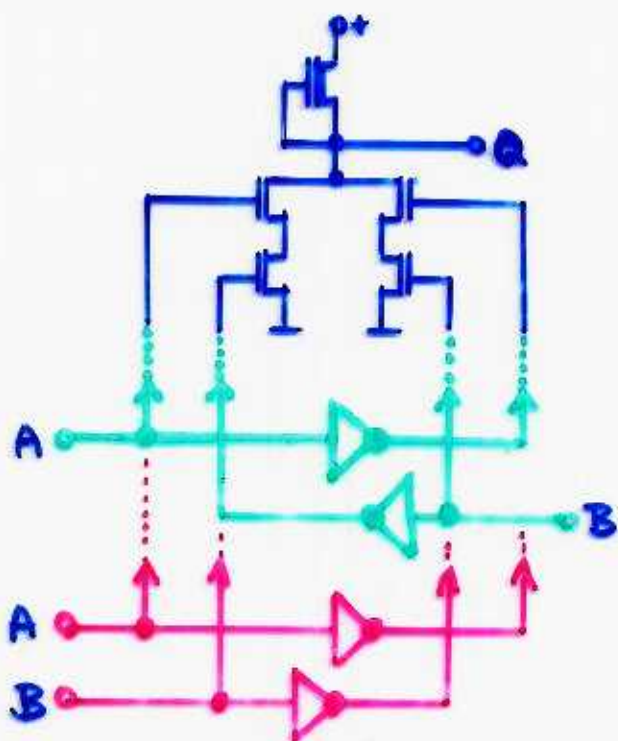


XY

	Z	
	0	1
AB		
00	00	11
01	01	00
11	11	00
10	10	00

↑ AB-Übernahme (Inverter-Plot)
 ↑ XY identisch (NOR-Plot)

Äquivalenz (statisch) ↗
 Antivalenz (statisch) ↘



ÄQUIVALENZ:

	Q	
	0	1
AB		
00	1	0
01	0	1

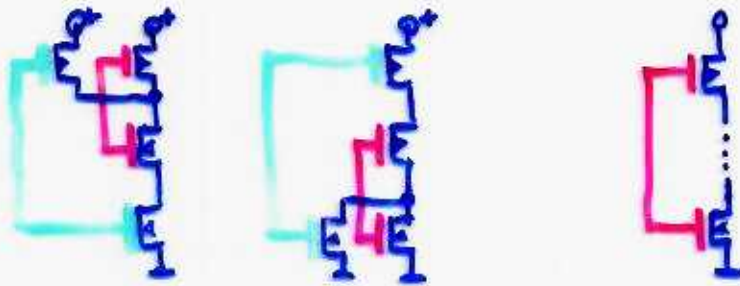
ANTIVALENZ:

	Q	
	0	1
AB		
00	0	1
01	1	0

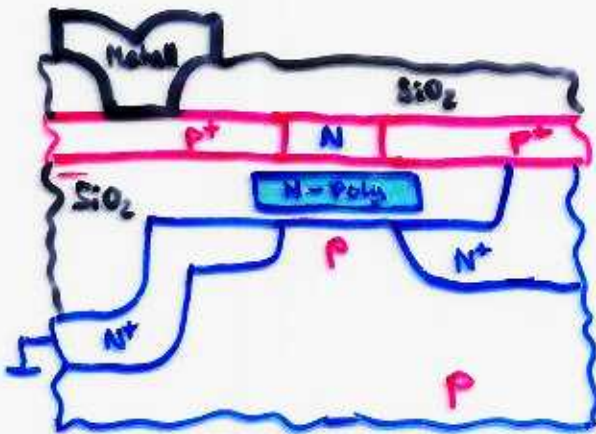
3D-CMOS

B. Hoeflinger, S.T. Liu, B. Vajdic „A Three-Dimensional CMOS Design Methodology“

CMOS - typisch: gemeinsamer Gateanschluss zweier Transistoren (pudn)



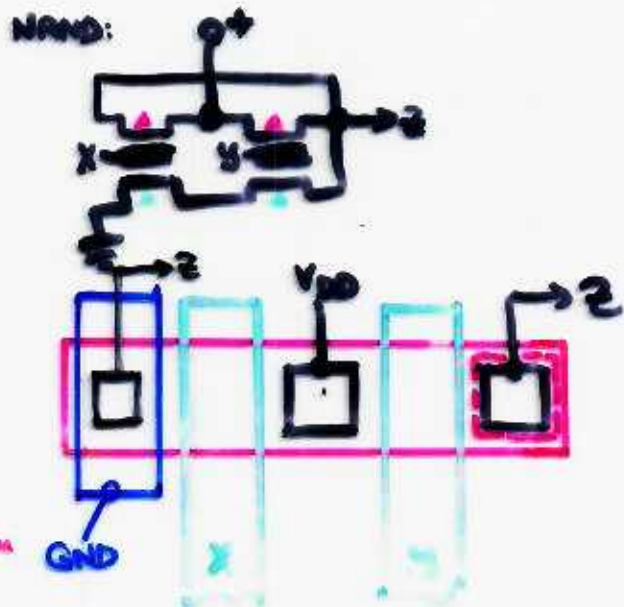
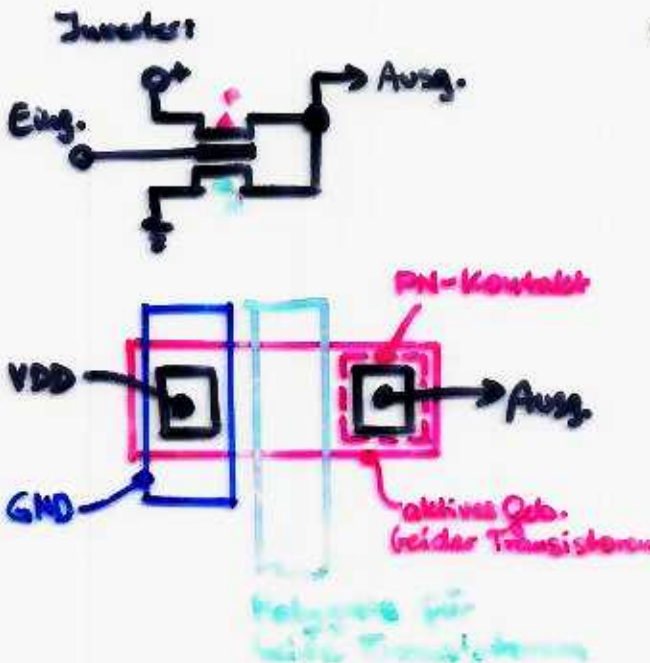
Idee: n- und p-Kanal - Gate identisch: beide Gates und beide Transistoren (akt. Gebiet) mit few. identischer Maske strukturiert.



Effekte: zB Volladder:

Bulk-CMOS: $13 \times 45 = 195 \lambda^2$
 SOI: $11 \times 42 = 132 \lambda^2$
 3D-CMOS: $8 \times 7 = 56 \lambda^2$

- kleiner als NMOS
- Verlustleistungsfrei (statisch)
- minimal denkbar: 5+4 Masken
 - ↳ Fehlerarm entwerfen,
 - ↳ CAD-freundlich



— : Metall-P+ Kontakt

— : aktives Transistorgebiet

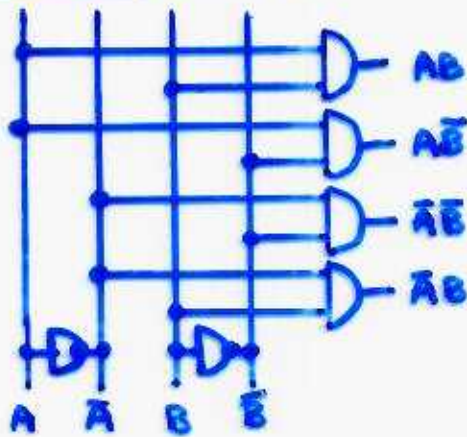
— : Polygate

— : vergrabener Bulkanschluss

Programmierbare Logik:

DECODER

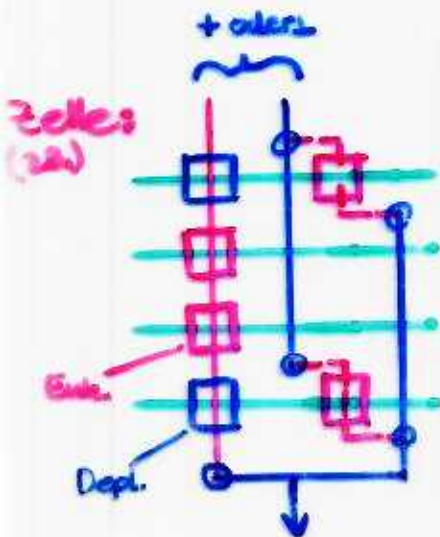
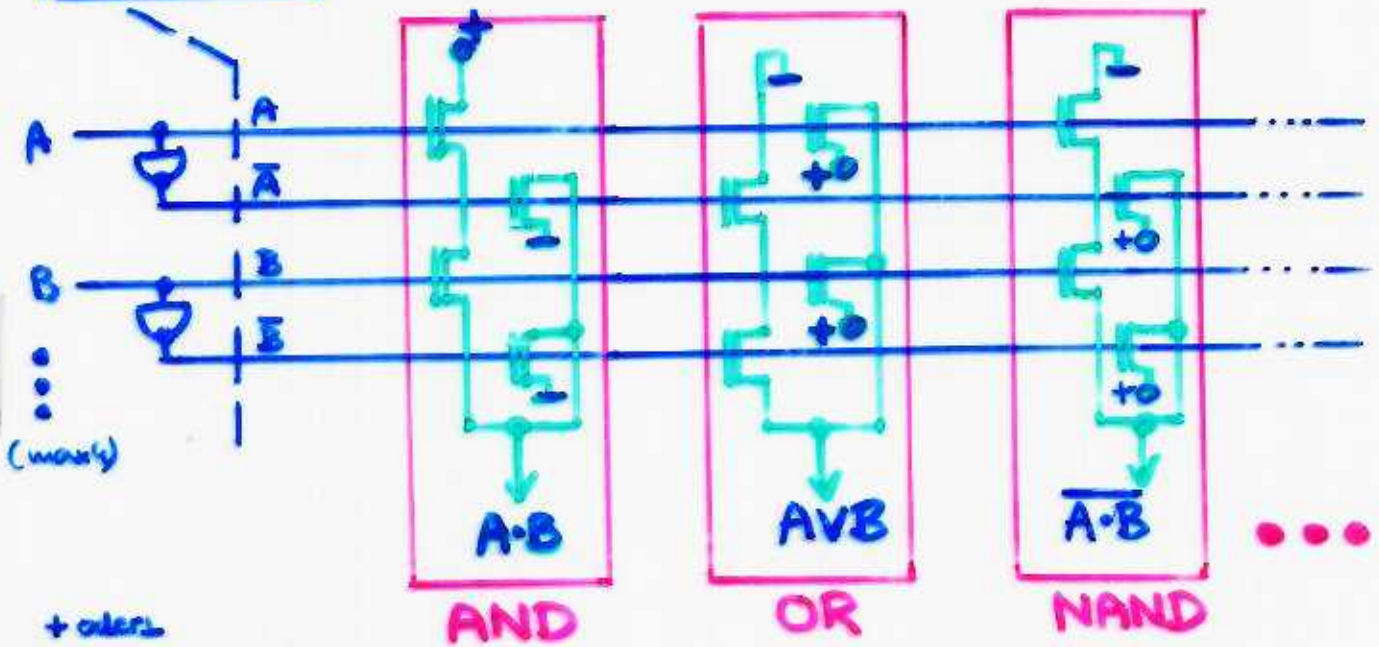
klassisch (z.B. 2bit):



Nachteile: • hohes P_V
• schlecht „ermannbar“

A	B	AB	$\bar{A}B$	$A\bar{B}$	$\bar{A}\bar{B}$
0	0				1
0	1			1	
1	0		1		
1	1	1			

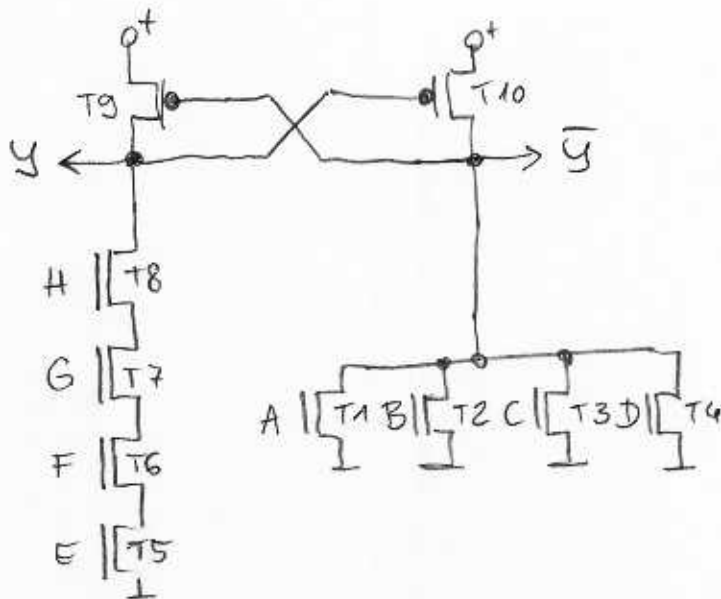
„programmierbar“



Vorteile:

- $P_V \downarrow$
 - „ermannbar“
 - bei Verwendung RAL-codierter Terme (A und \bar{A} , ...)
- Verlustleistungsfreiheit (statisches P_V)
und Vermeidung „wildes“ Logik!

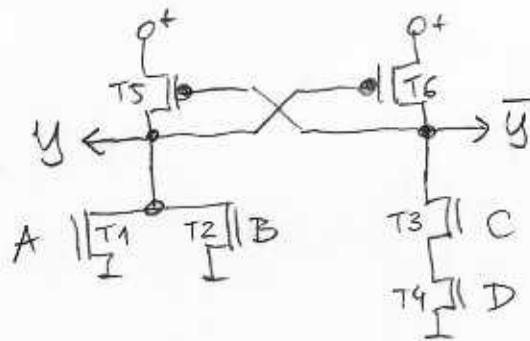
IAND4, IOR4 (Spiegellogik - Jantes)



A	B	C	D	E	F	G	H	Y	\bar{Y}
a	b	c	d	\bar{a}	\bar{b}	\bar{c}	\bar{d}	OR	NOR
\bar{a}	\bar{b}	\bar{c}	\bar{d}	a	b	c	d	NAND	AND

1 Layout mit 2 Pins für AND/NAND bzw. OR/NOR zu bezeichnen: 2 Zellen

IANDZ, IORZ (Spiegellogik-Gatter)



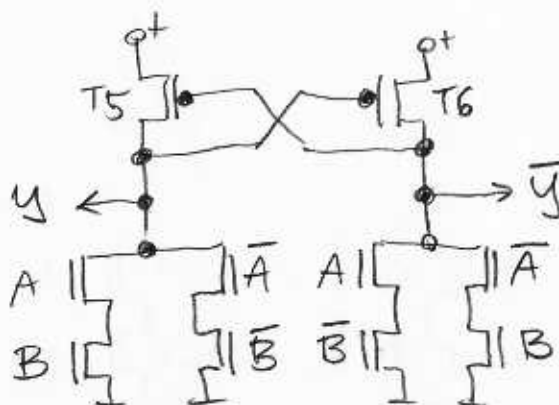
A	B	C	D	y	\bar{y}
a	b	\bar{a}	\bar{b}	NOR	OR
\bar{a}	\bar{b}	a	b	AND	NAND

1 layout mit 2 Pinouts für AND/NAND bzw. OR/NOR
zu berechnen: 2 Zellen!

$$\begin{array}{ll}
 T1, T2 & (B/L) = 2/1 \\
 T3, T4 & (B/L) = 3/1 \\
 T5, T6 & (B/L) = 6/1
 \end{array}$$

IANT2

(Spiegellogik-Gatter)



A	B	\bar{A}	\bar{B}	Y	\bar{Y}
a	b	\bar{a}	\bar{b}	ANT	AEQ

1 layout mit 1 Pinout für ANTVALENZ-Flut.